

2SA953

Rev.E Mar.-2016

/ Descriptions

TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

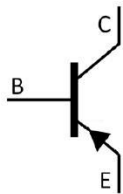
h_{FE} , V_{CEO}

High total power dissipation, high h_{FE} and high V_{CEO} .

/ Applications

Audio frequency amplifier and driver stage.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	90~180	135~270	200~400

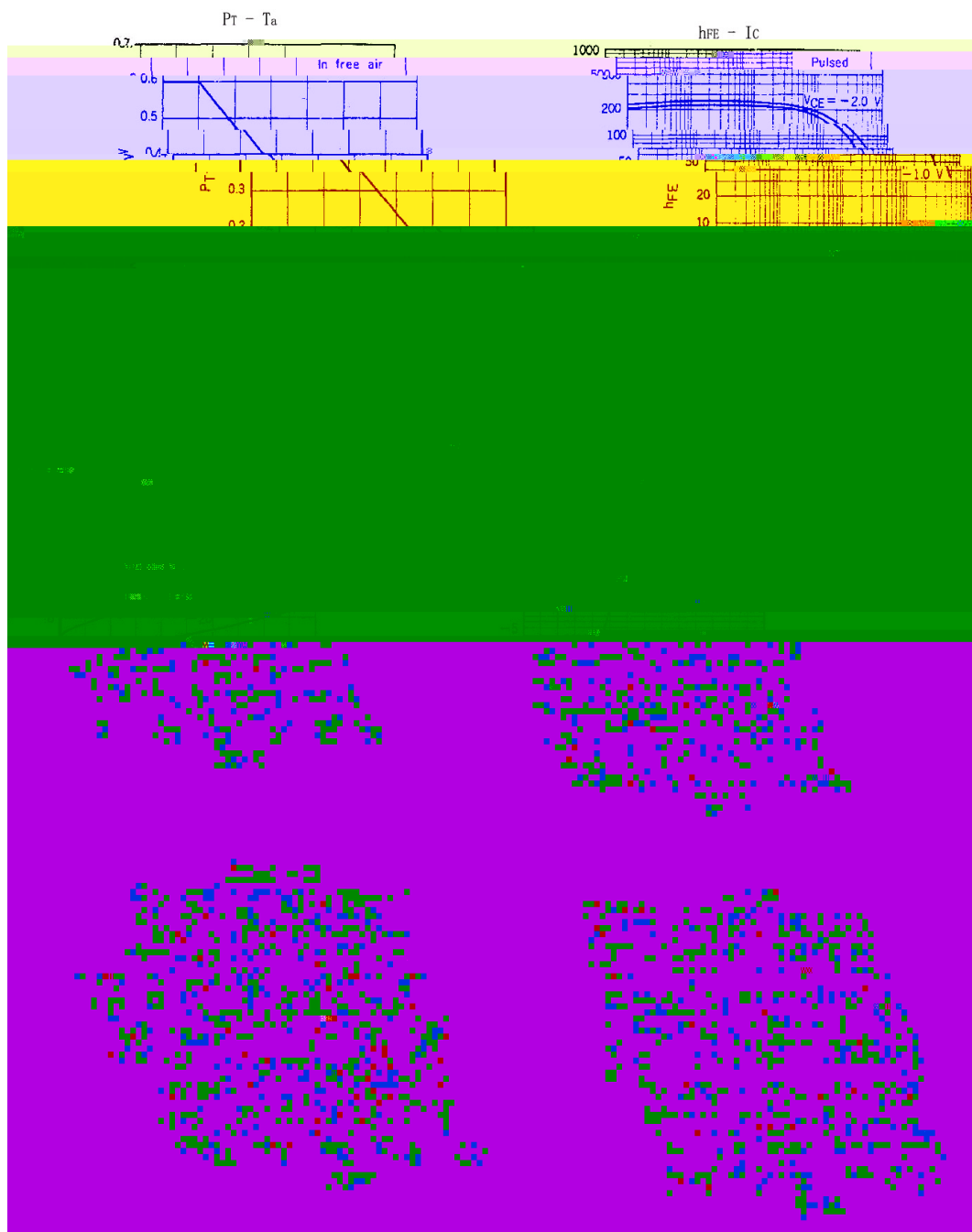
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-300	mA
Base Current – Continuous	I_B	-60	mA
Collector Power Dissipation	P_C	600	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60V$ $I_E=0$			-0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-50mA$	90		400	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-300mA$	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-300mA$ $I_B=-30mA$		-0.15	-0.60	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-300mA$ $I_B=-30mA$		-0.85	-1.20	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-6.0V$ $I_C=-10mA$		-0.66	-0.70	V
Transition Frequency	f_T	$V_{CE}=-6.0V$ $I_C=-10mA$	50	100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6.0V$ $I_E=0$ $f=1.0MHz$		13	25	pF

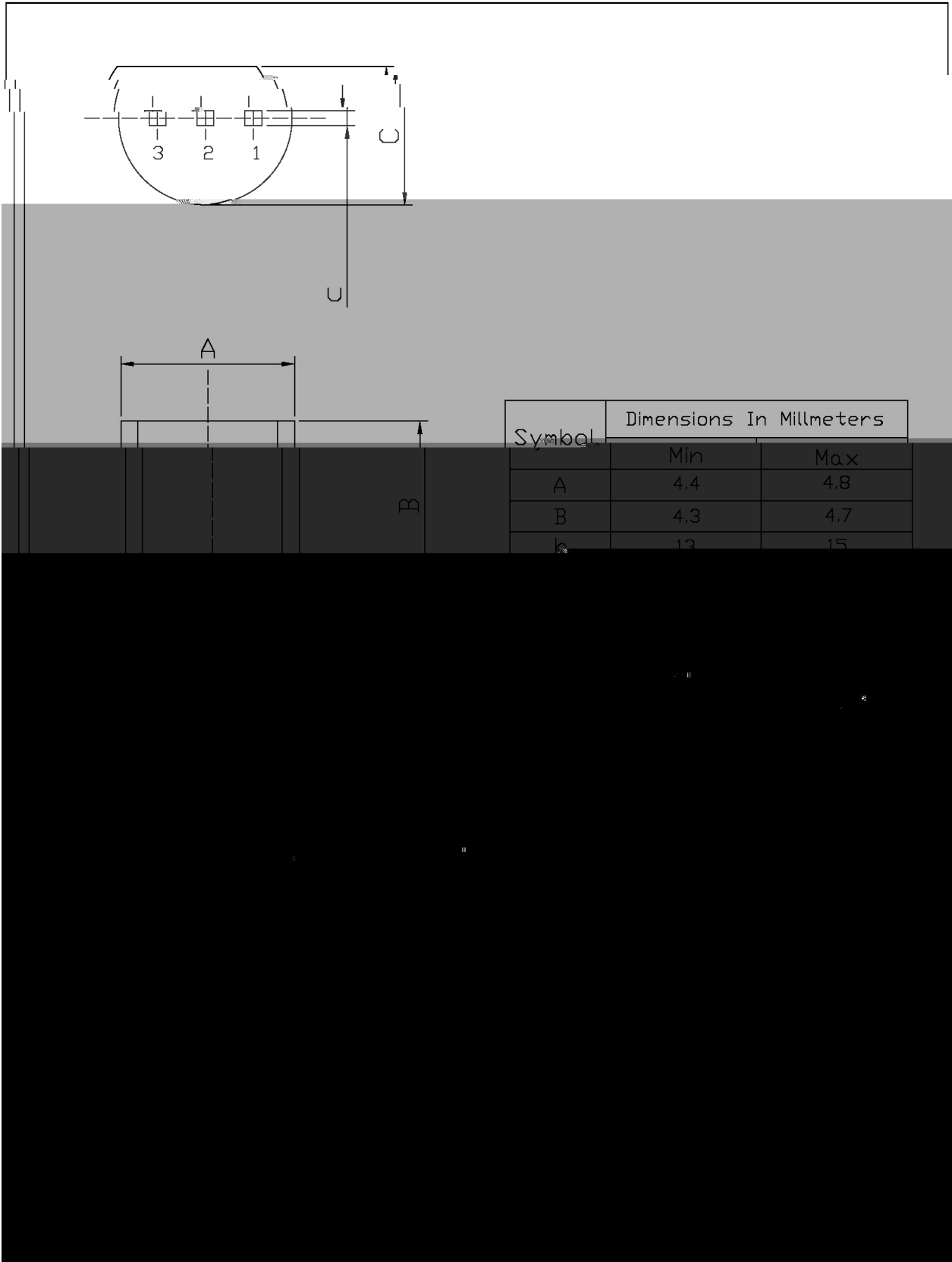
/ Electrical Characteristic Curve



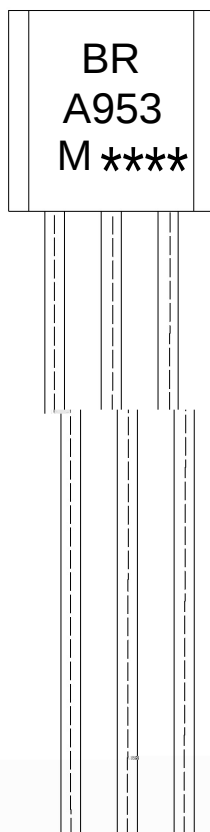
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



BR:

A953

M:

h_{FE}

Note:

BR:

Company Code.

A953:

Product Type.

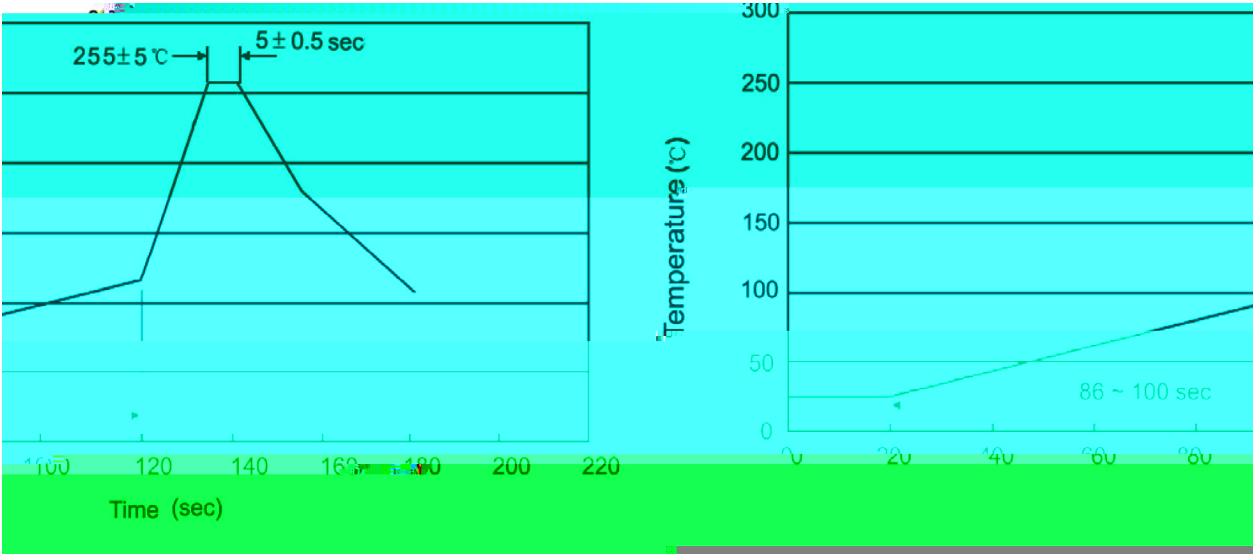
M:

h_{FE} Classifications Symbol

****:

Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:
1.Preheating:25~150 ,eri(:)1e99:

1 25 150 60 90sec;